



America Semiconductor

**Silicon Standard
Recovery Diode**

**1N3671A thru
1N3673AR**

V_{RRM} = 50 V - 1000 V

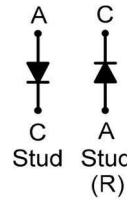
I_F = 12 A

Features

- High Surge Capability
- Types up to 1000 V V_{RRM}

Note:

1. Standard polarity: Stud is cathode.
2. Reverse polarity (R): Stud is anode.
3. Stud is base.



DO-4 Package



Maximum ratings, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	1N3671A (R)	1N3673A (R)	Unit
Repetitive peak reverse voltage	V _{RRM}		800	1000	V
RMS reverse voltage	V _{RMS}		560	700	V
DC blocking voltage	V _{DC}		800	1000	V
Continuous forward current	I _F	T _C ≤ 150 °C	12	12	A
Surge non-repetitive forward current, Half Sine Wave	I _{F,SM}	T _C = 25 °C, t _p = 8.3 ms	240	240	A
Operating temperature	T _j		-65 to 200	-65 to 200	°C
Storage temperature	T _{stg}		-65 to 200	-65 to 200	°C

Electrical characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	1N3671A (R)	1N3673A (R)	Unit
Diode forward voltage	V _F	I _F = 12 A, T _j = 25 °C	1.1	1.1	V
Reverse current	I _R	V _R = 50 V, T _j = 25 °C	10	10	μA
		V _R = 50 V, T _j = 175 °C	15	15	mA

Thermal characteristics

Thermal resistance, junction - case	R _{thJC}		2.00	2.00	°C/W
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